



HID80R400-P

N-Channel SiC Power MOSFET

● Features:

- High Blocking Voltage with Low On-Resistance
- High Speed Switching with Low Capacitance
- Easy to Parallel and Simple to Drive

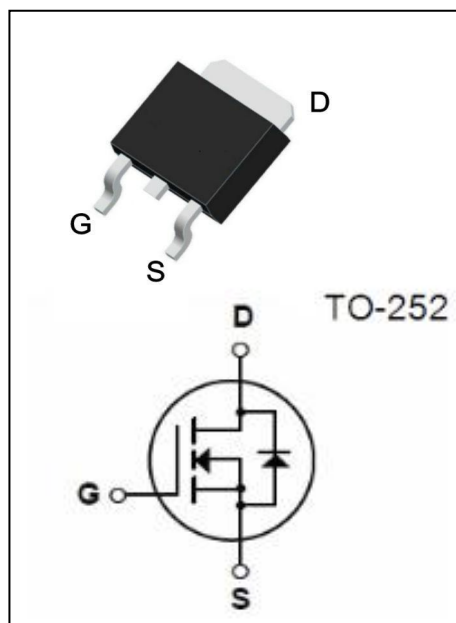
● Benefits:

- Higher System Efficiency
- Reduced Cooling Requirements
- Increased Power Density
- Increased System Switching Frequency

● Applications:

- Renewable Energy
- EV Battery Chargers
- High Voltage DC/DC Converters
- Switch Mode Power Supplies

V_{DSS}	800	V
$R_{DS(on)}(Typ)$	400	mΩ
$I_D@25^{\circ}C$	11	A



Maximum Ratings ($T_C=25^{\circ}C$ unless otherwise specified)

Symbol	Parameter	Test Conditions	Value	Unit
V_{DSmax}	Drain-Source Voltage	$V_{GS}=0V$, $I_D=250\mu A$	800	V
V_{GSmax}	Gate-Source Voltage	Absolute maximum values	-8/+20	V
V_{GSop}	Gate-Source Voltage	Recommended operational values	0/+18	V
I_D	Continuous Drain Current	$V_{GS}=18V$, $T_C=25^{\circ}C$	11	A
		$V_{GS}=18V$, $T_C=100^{\circ}C$	7.8	
$I_{D(pulse)}$	Pulsed Drain Current	Pulse width t_p limited by T_{Jmax}	27.5	A
P_D	Power Dissipation	$T_C=25^{\circ}C$, $T_J=175^{\circ}C$	38	W
T_J , T_{STG}	Operating Junction and Storage Temperature	--	-40 to +175	$^{\circ}C$

Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JC}$	Thermal Resistance from Junction to Case	3.95	--	$^{\circ}C/W$
$R_{\theta JA}$	Thermal Resistance from Junction to Ambient	--	69	

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Electrical Characteristics($T_C=25^{\circ}\text{C}$ unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu A$	800	--	--	V
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=1.0mA$	2.3	3.5	4.8	V
		$V_{DS}=V_{GS}, I_D=1.0mA, T_J=175^{\circ}\text{C}$	--	2.5	--	
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS}=800V, V_{GS}=0V$	--	0.5	30	μA
I_{GSS+}	Gate-Source Leakage Current	$V_{DS}=0V, V_{GS}=20V$	--	20	250	nA
I_{GSS-}	Gate-Source Leakage Current	$V_{DS}=0V, V_{GS}=-8V$	--	-20	-250	nA
$R_{DS(on)}$	Drain-Source On-State Resistance	$V_{GS}=18V, I_D=3.6A$	--	400	500	m Ω
		$V_{GS}=15V, I_D=3.6A$	--	570	--	m Ω
C_{iss}	Input Capacitance	$V_{GS}=0V, V_{DS}=600V,$ $f=1MHz$	--	191	--	pF
C_{oss}	Output Capacitance		--	15.2	--	
C_{rss}	Reverse Transfer Capacitance		--	1.3	--	
$t_{d(on)}$	Turn-On Delay Time	$V_{DS}=400V, V_{GS}=18V,$ $I_D=3.6A, R_{G(ext)}=5\Omega$	--	8.8	--	ns
t_r	Rise Time		--	40	--	
$t_{d(off)}$	Turn-Off Delay Time		--	13.1	--	
t_f	Fall Time		--	39.8	--	
Q_G	Total Gate Charge	$V_{DS}=400V$ $V_{GS}=18V$ $I_D=3.6A$	--	19.2	--	nC
Q_{GS}	Gate to Source Charge		--	6.3	--	
Q_{GD}	Gate to Drain Charge		--	3.8	--	

Reverse Diode Characteristics($T_C=25^{\circ}\text{C}$ unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V_{SD}	Diode Forward Voltage	$V_{GS}=0V, I_{SD}=1.8A$	--	3.5	--	V
		$V_{GS}=0V, I_{SD}=1.8A, T_J=175^{\circ}\text{C}$	--	3.1	--	
I_S	Continuous Diode Forward Current	--	--	--	11	A
t_{rr}	Reverse Recover Time	$V_{DD}=400V, I_{SD}=3.6A,$ $dI_F/dt=850A/\mu s$	--	11.6	--	ns
Q_{rr}	Reverse Recovery Charge		--	35	--	nC

Typical Performance Characteristics

Fig 1. Output Characteristics $T_j = 25^\circ\text{C}$

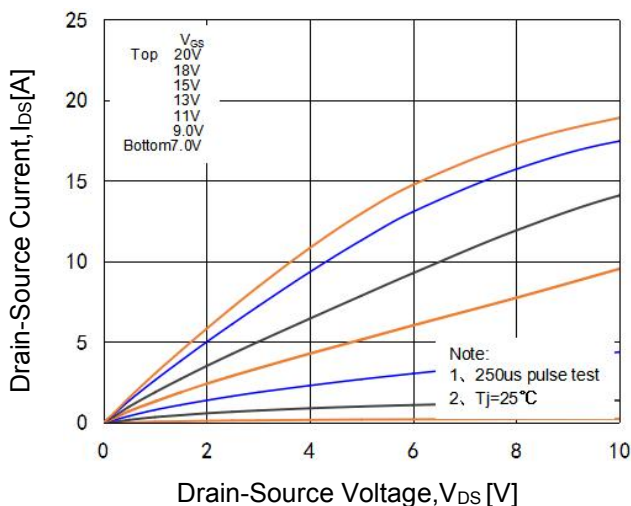


Fig 2. Transfer Characteristic for Various Junction Temperature

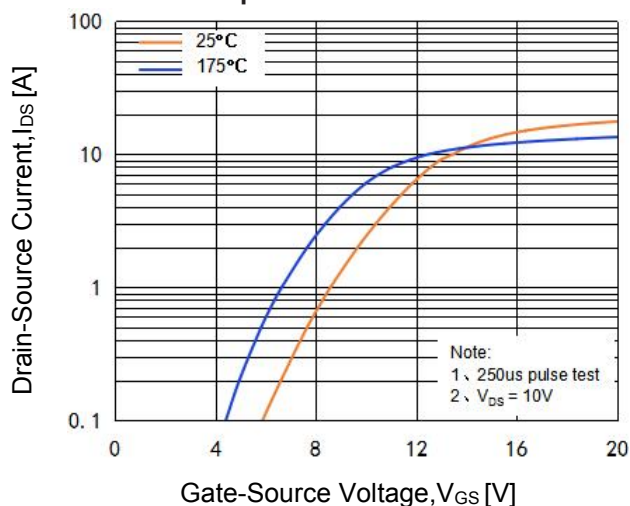


Fig 3. On-Resistance vs. Drain Current For Various Temperature

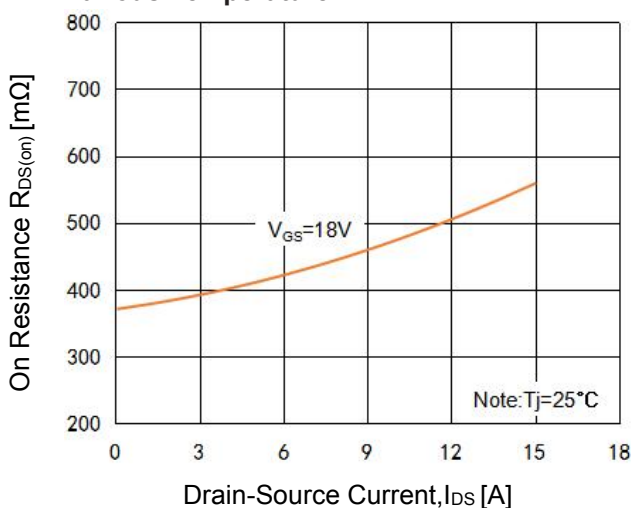


Fig 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

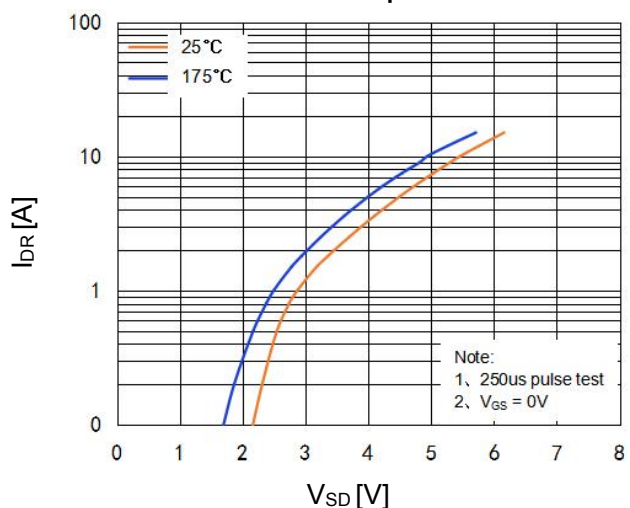


Fig 5. Capacitance vs. Drain-Source Voltage

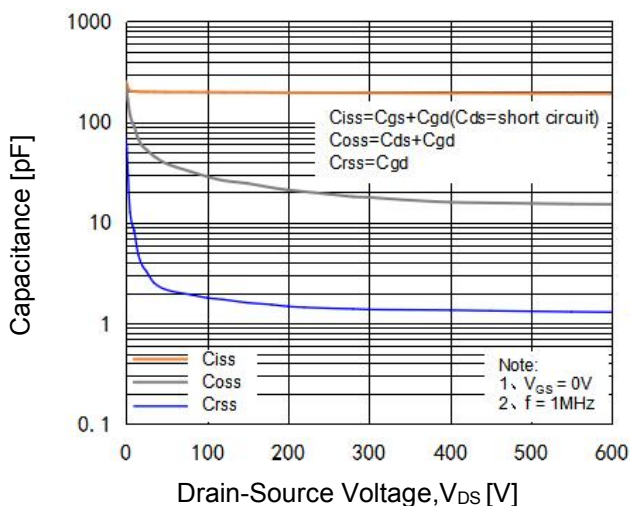


Fig 6. Gate Charge Characteristics

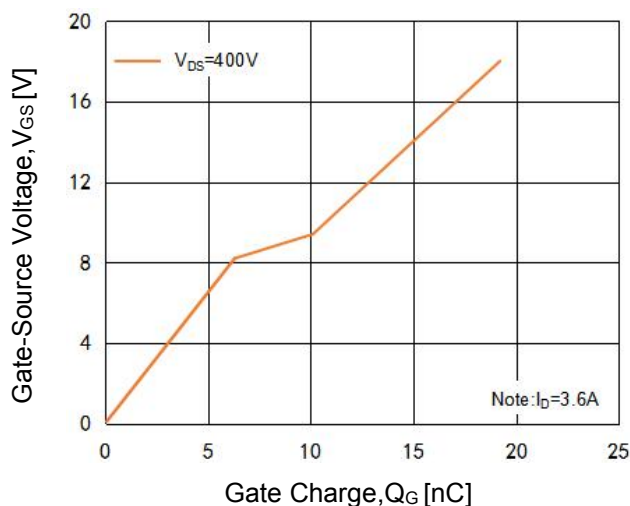


Fig 7. Threshold Voltage vs. Temperature

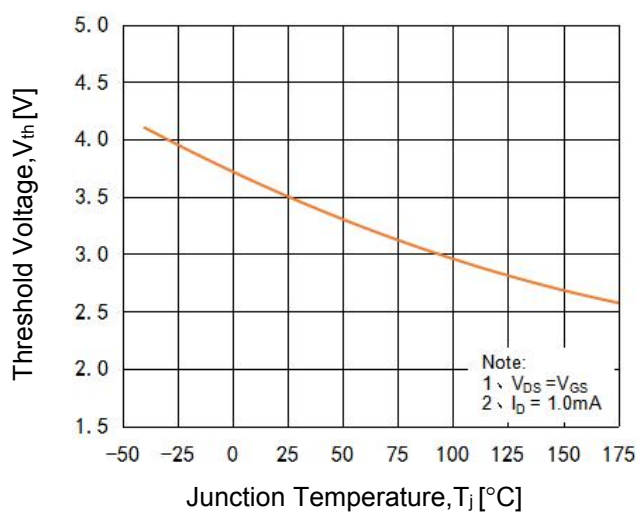


Fig 8. Normalized On-Resistance vs. Temperature

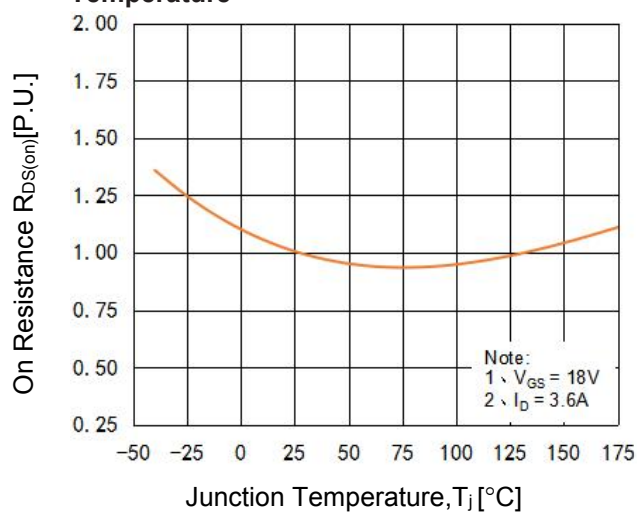


Fig 9. Maximum Power Dissipation Derating vs. Case Temperature

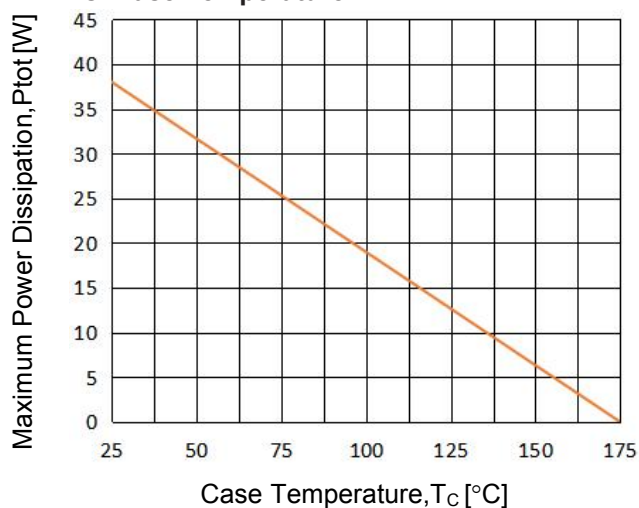
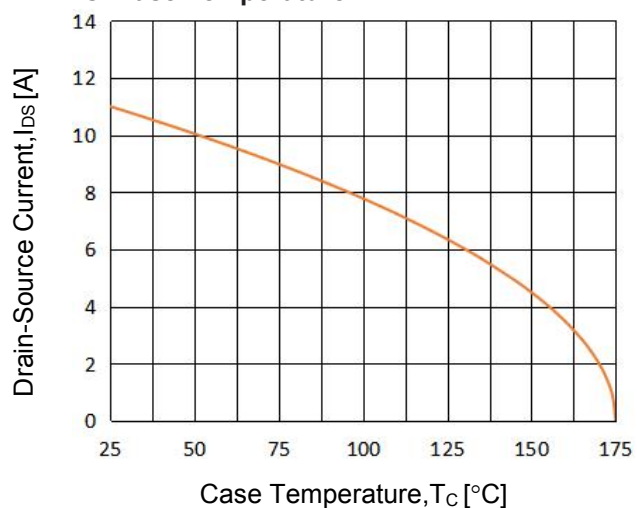


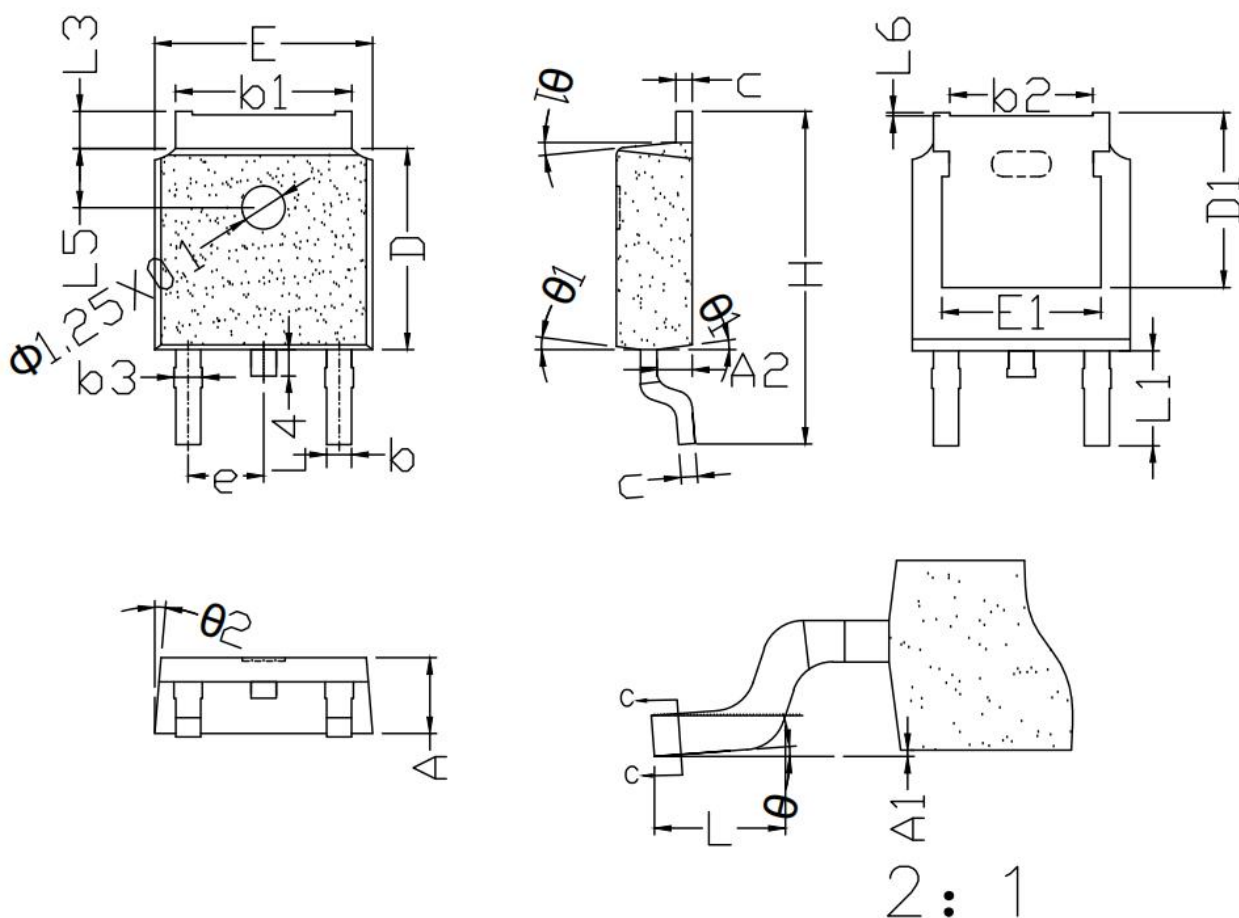
Fig 10. Continuous Drain Current Derating vs. Case Temperature



TO-252 Package Dimensions

UNIT: mm

SYMBOL	min	nom	max	SYMBOL	min	nom	max
A	2.20	2.30	2.40	E	6.40	6.55	6.70
A1	0.00	--	0.15	E1	4.65	4.80	4.95
A2	0.85	1.00	1.15	H	9.80	10.10	10.40
b	0.68	0.78	0.88	L	1.35	1.55	1.75
b1	5.18	5.33	5.48	L1	--	2.90	--
b2	4.17	4.32	4.47	L3	0.90	--	1.20
b3	0.75	0.85	0.95	L4	0.70	0.85	1.00
c	0.45	--	0.55	L5	1.60	1.80	2.00
D	5.90	6.05	6.20	L6	0.00	0.04	0.12
D1	--	5.30	--	θ (度)	0	--	5
e	--	2.30	--	$\theta 1$ (度)	5	7	9
				$\theta 2$ (度)	5	7	9



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- 注意事项：
- 1、在电路设计时请不要超过器件的最大额定值，否则会影响整机的可靠性。
 - 2、MOSFET产品为静电敏感型器件，使用时应注意采取防静电保护措施，如佩戴防静电手环、设备接地等。
 - 3、如需安装散热片，请注意控制扭力大小及散热片的平整度。
 - 4、该规格书由华科公司制作，并可能不定期更改，恕不另行通知。
 - 5、如有疑问，请及时联系我司销售代表。

版本履历表：

序号	版本号	修改时间	修改记录
1	V1.0	2025-3-5	首次发行